

NEW PRODUCT

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>A</sub> = +25°C
30V	30mΩ @ V <sub>GS</sub> = 10V	6A
	42mΩ @ V <sub>GS</sub> = 4.5V	5A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

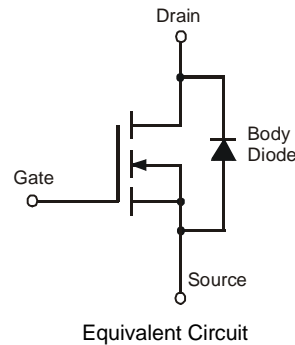
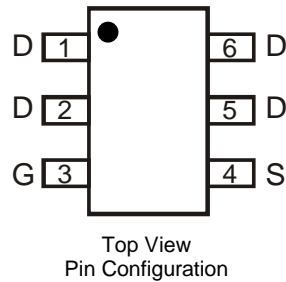
- DC-DC Converters
- Power Management Functions
- Backlighting

## Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.013 grams (Approximate)

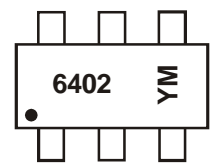


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG6402LVT-7	TSOT26	3,000/Tape & Reel
DMG6402LVT-13	TSOT26	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



6402 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: G = 2019)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	~	2019	2020	2021	2022	2023
Code	Y	~	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.0 4.8	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	7.5 5.9	A
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	5.0 4.0	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6 4.8	A
Maximum Body Diode Forward Current (Note 5)			I <sub>S</sub>	2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	31	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.75	W
	T <sub>A</sub> = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	72	°C/W
	t < 10s		50	
Thermal Resistance, Junction to Case (Note 5)		R <sub>θJC</sub>	23	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.5	2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	22	30	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7A
		—	32	42		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.6A
Forward Transfer Admittance	Y <sub>fs</sub>	—	10	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 7A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	498	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	52	—		
Reverse Transfer Capacitance	C <sub>riss</sub>	—	45	—		
Gate Resistance	R <sub>G</sub>	—	2.4	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	11.4	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.8A
Gate-Source Charge	Q <sub>gs</sub>	—	1.4	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.4	—	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 2.6Ω, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	6.2	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	13.9	—		
Turn-Off Fall Time	t <sub>F</sub>	—	2.8	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

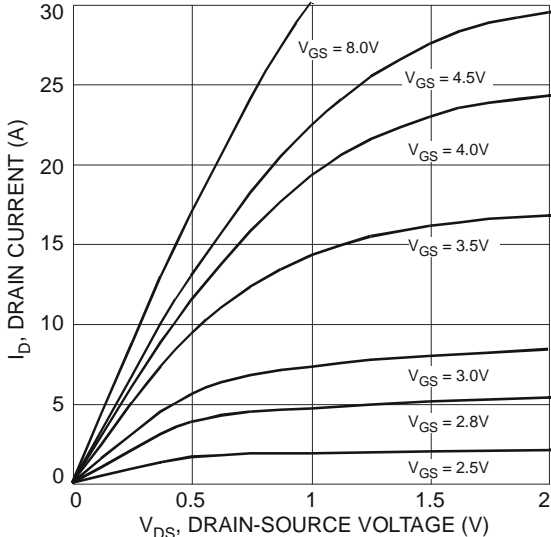


Fig. 1 Typical Output Characteristics

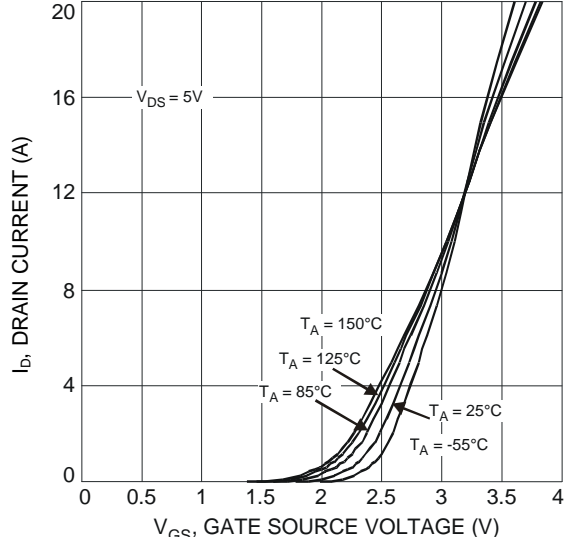


Fig. 2 Typical Transfer Characteristics

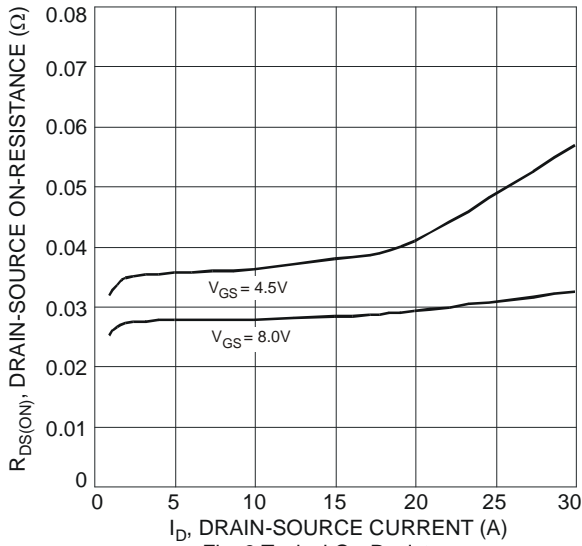


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

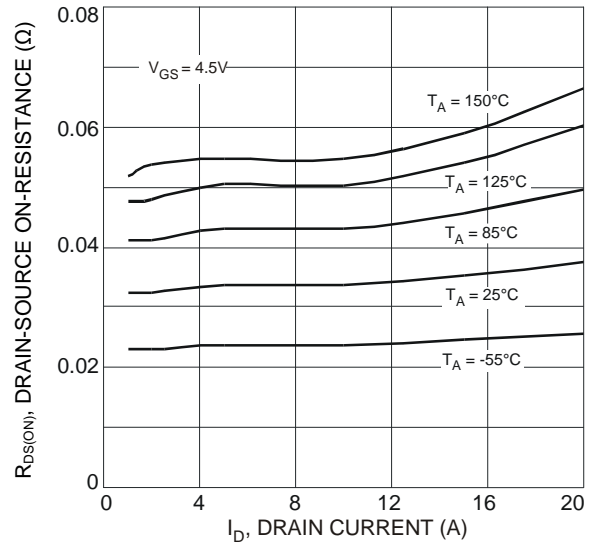


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

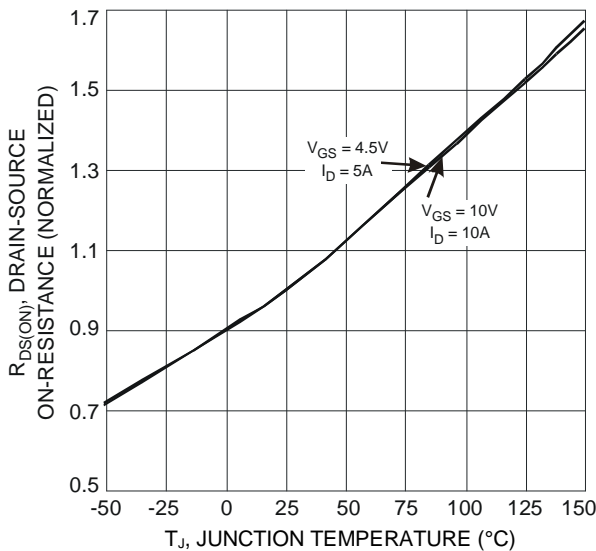


Fig. 5 On-Resistance Variation with Temperature

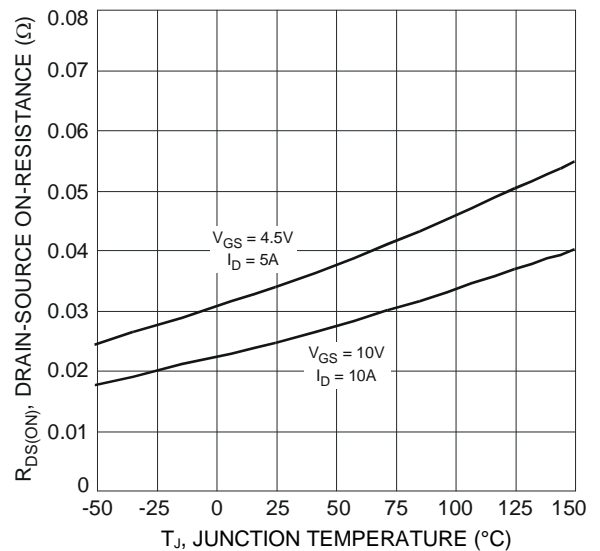


Fig. 6 On-Resistance Variation with Temperature

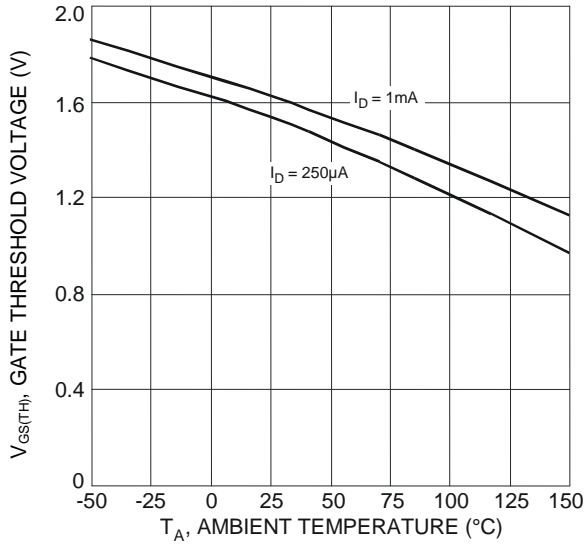


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

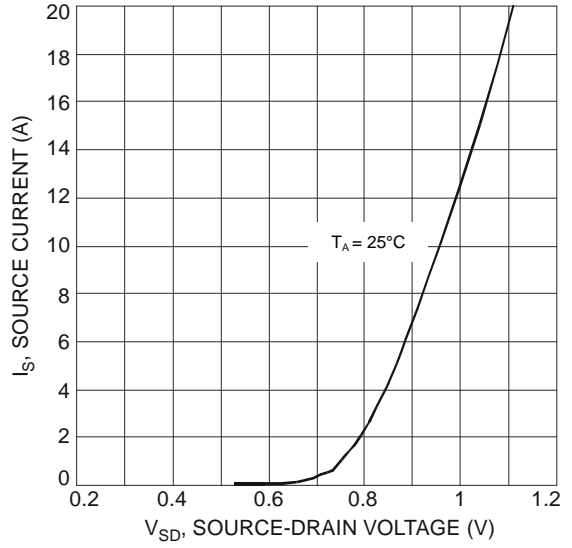


Fig. 8 Diode Forward Voltage vs. Current

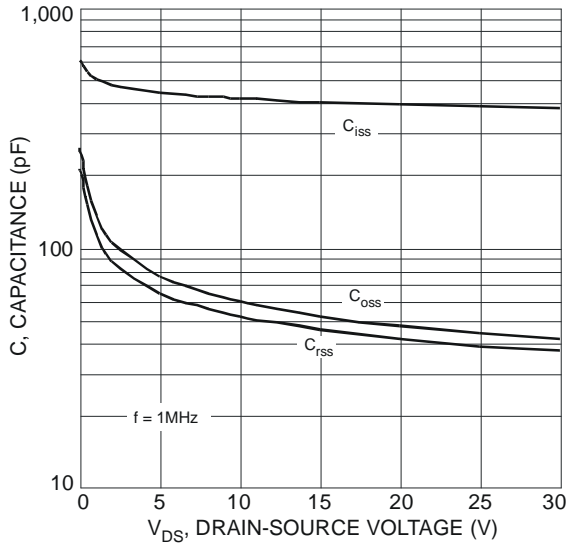


Fig. 9 Typical Capacitance

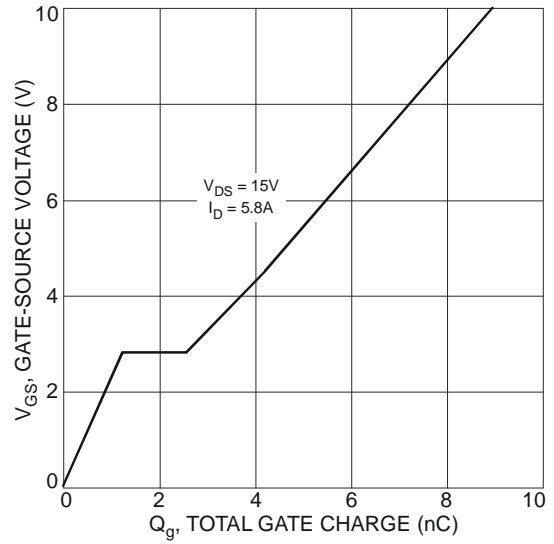


Fig. 10 Gate-Charge Characteristics

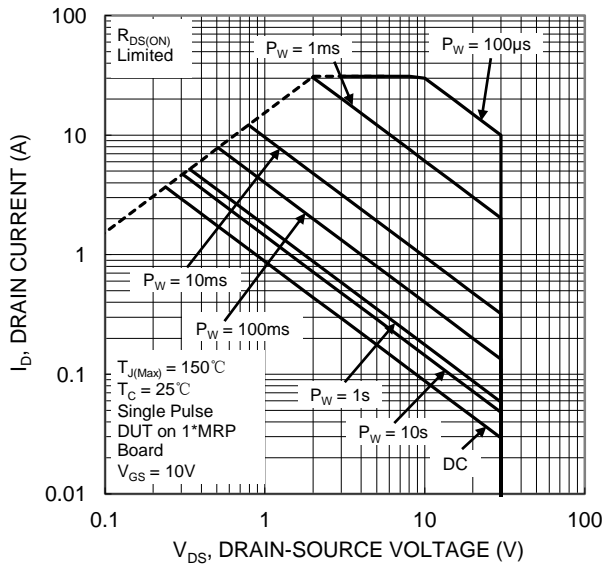


Fig. 11 SOA, Safe Operation Area

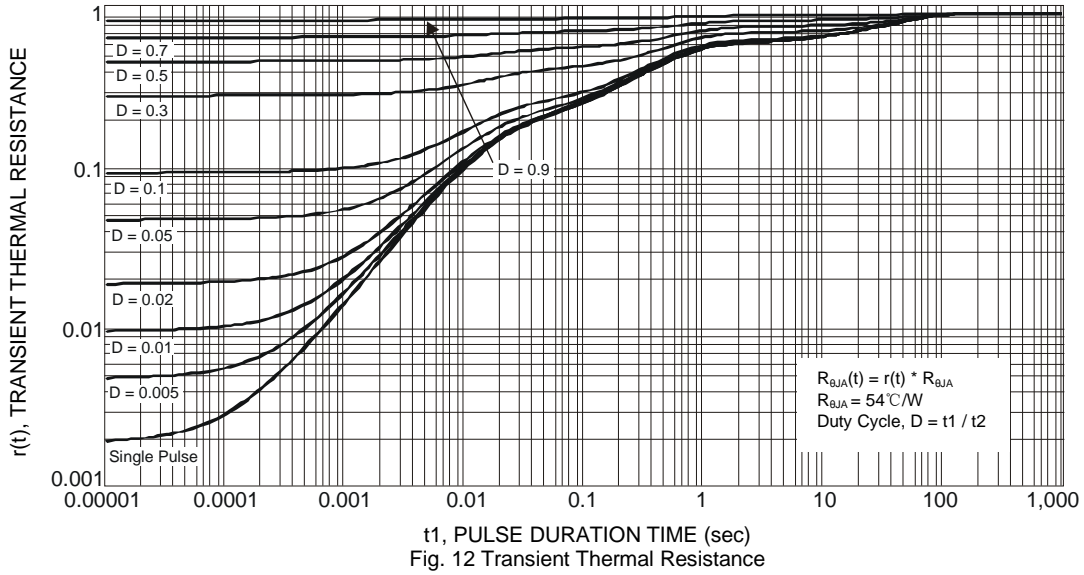
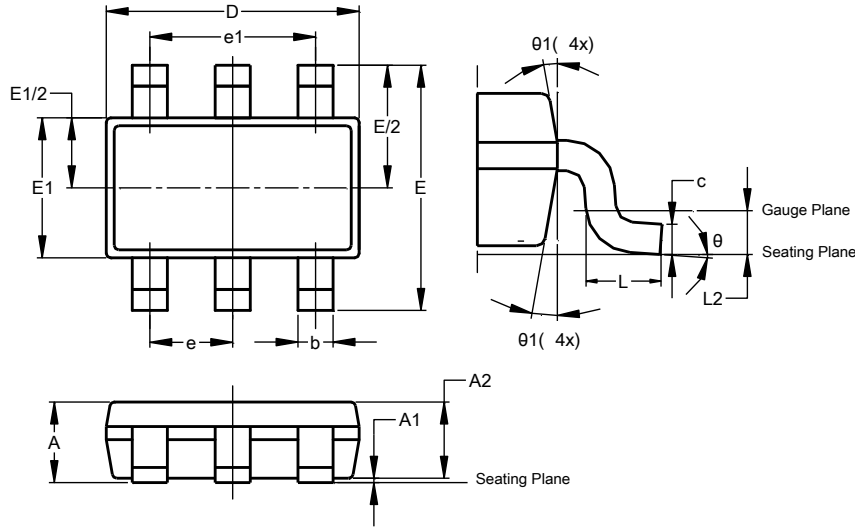


Fig. 12 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TSOT26**

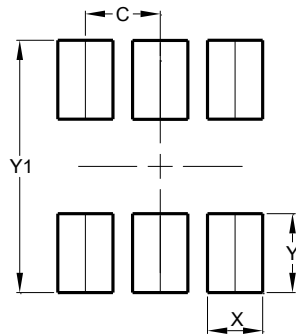


TSOT26			
Dim	Min	Max	Typ
A	-	1.00	-
A1	0.010	0.100	-
A2	0.840	0.900	-
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	-
c	0.120	0.200	-
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	-
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	-
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TSOT26**



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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